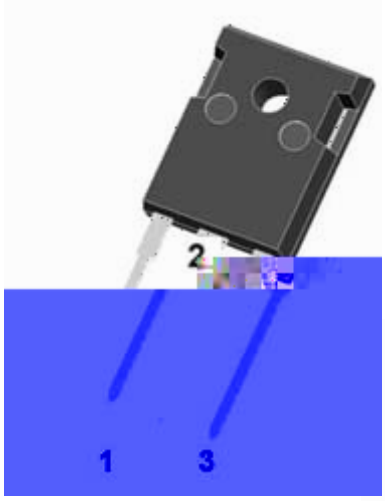
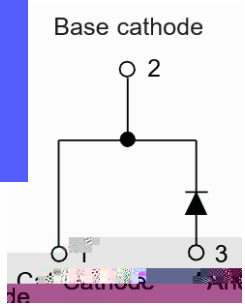
RoHS
COMPLIANT





- Adopt FRED chip
- Low forward Voltage drop
- Fast reverse recovery time
- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability

●Typical applications are in switching power supplies, . converters, freewheeling diodes, and reverse battery protection.

- : TO-247AC
  Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant
- : Tin plated leads, solderable per J-STD-002 and JESD22-B102
- : As marked

■ (Tj=25℃ Unless otherwise specified）

Device marking code			MURL3065P
Repetitive Peak Reverse Voltage	V_{RRM}	V	650
Average Rectified Output Current @60Hz sine wave, R-load, Tc(FIG.1)	I_O	A	30
Surge(Non-repetitive)Forward Current @60Hz half sine-wave, 1 cycle, Tj=25℃	I_{FSM}	A	450
Current Squared Time @1ms≤t≤8.3ms Tj=25℃	I^2t	A^2s	840
Single Pulse Avalanche Energy @ Tj=25℃,L=15mH	EAS	mJ	261
Storage Temperature	Tstg		-55 ~ +175
Junction Temperature	Tj		-55 ~ +175
Typical Junction capacitance @4V,1MHz	Cj	pF	190
Mounting torque @recommend torque：5kg cm Tor kg cm	Tor	kg cm	8

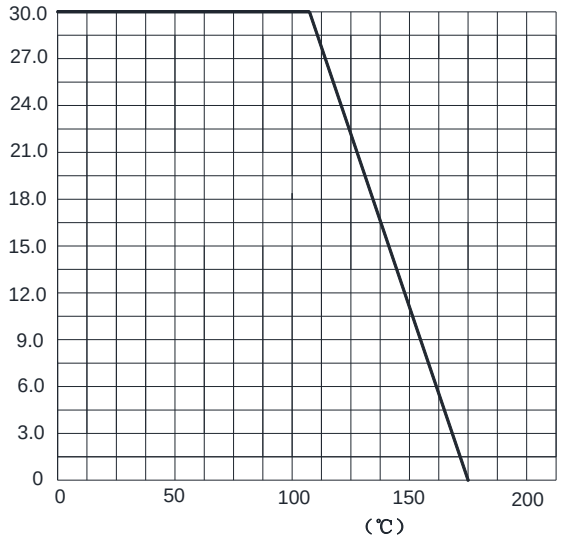
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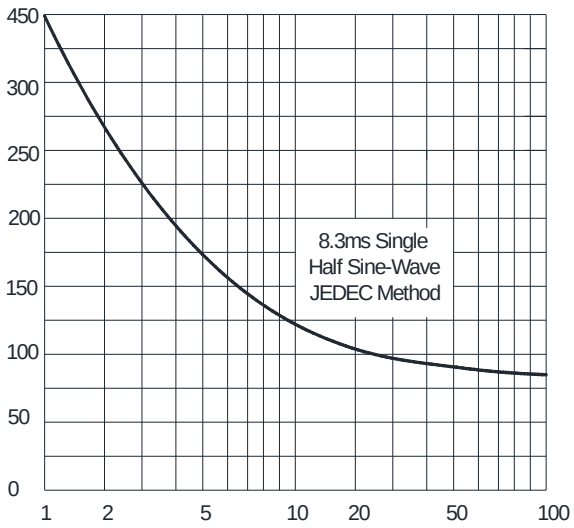
Instantaneous forward voltage drop per diode	V_{FM}	V	I_{FM}=30.0A @Tj=25		-	1.55	2.00
			I_{FM}=30.0A @Tj=150			1.25	1.60
DC reverse current at rated DC blocking voltage per diode	I_{RRM1}	uA	V_{RM}=V_{RRM} Tj=25		-	-	5.0
	I_{RRM2}		V_{RM}=V_{RRM} Tj=150		-	-	200
Reverse Recovery Time	Trr	ns	I_F=0.5A I_{RM}=1A I_{RR}=0.25A Tj=25		-	38	50
			Tj=25	I_F=30A di/dt=-200A/us V_{RM}=400V	-	100	-
			Tj=125		-	162	-
Peak recovery current	I_{RRM}	A	Tj=25		-	5.15	-
			Tj=125		-	12.88	-
Reverse recovery charge	Qrr	nC	Tj=25		-	262	-
			Tj=125		-	1043	-

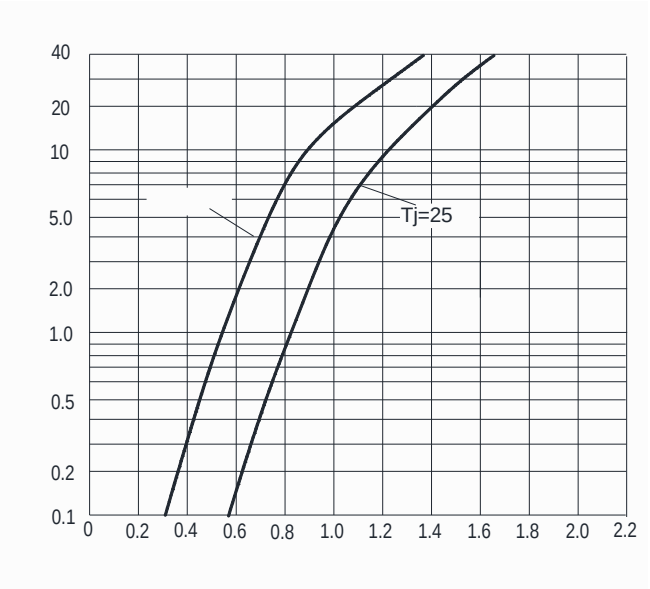
■ （Tj=25 Unless otherwise specified）

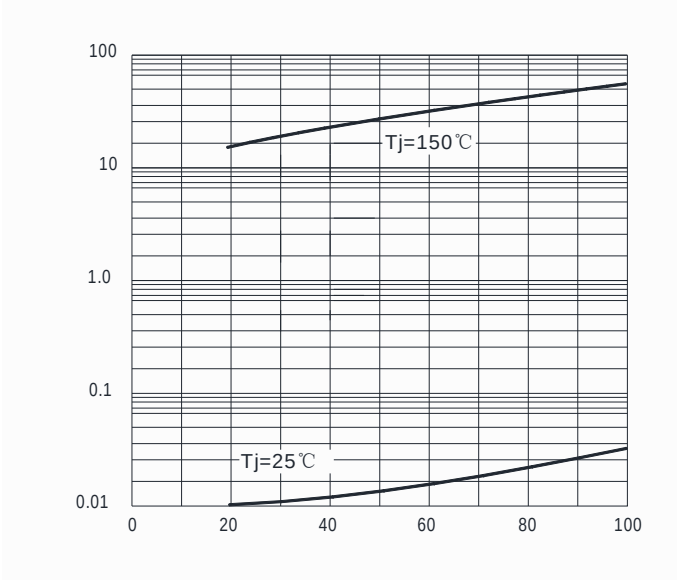
Thermal Resistance	Between junction and case	$R_{\theta J-C}$	/W	1.0
	Between junction and Air	$R_{\theta J-A}$	/W	50

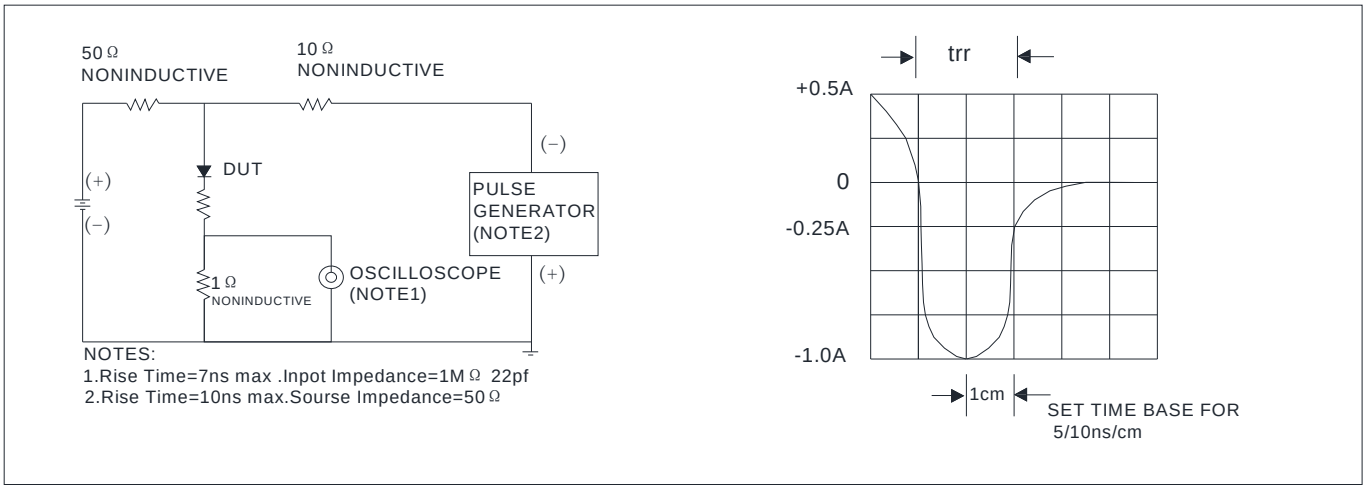
■ (Typical)



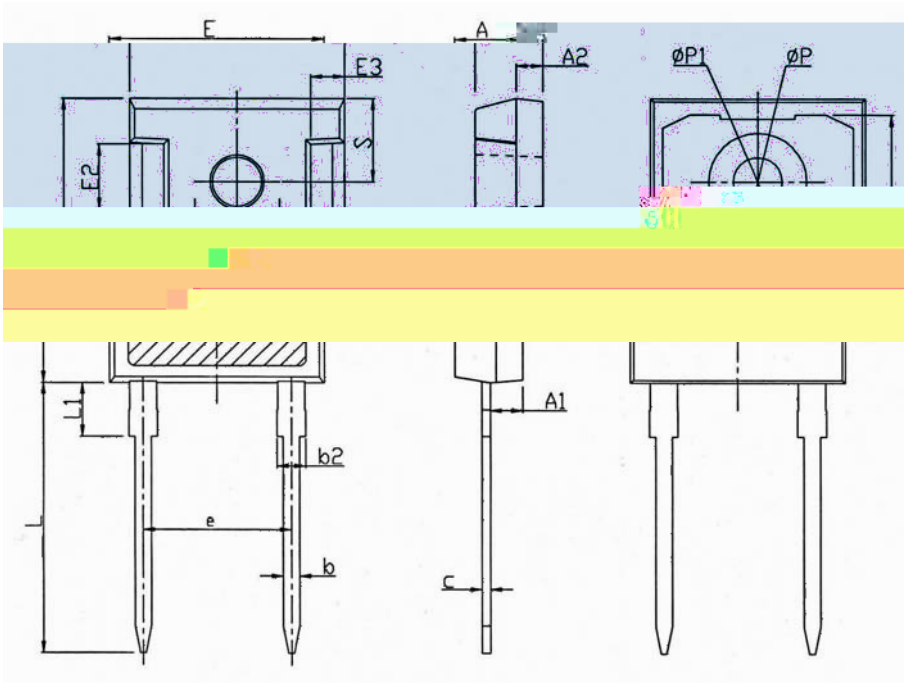



40
20
10
5.0
2.0
1.0
0.5
0.2
0.1
0
0.2
0.4
0.6
0.8
1.0
1.2
1.4
1.6
1.8
2.0
2.2
Tj=25


100
10
1.0
0.1
0.01
0
20
40
60
80
100
Tj=150℃
Tj=25℃


50Ω
NONINDUCTIVE
10Ω
NONINDUCTIVE
(+)
(−)
DUT
(−)
PULSE
GENERATOR
(NOTE2)
1Ω
NONINDUCTIVE
OSCILLOSCOPE
(NOTE1)
(+)
NOTES:
1.Rise Time=7ns max .Inpot Impedance=1MΩ 22pf
2.Rise Time=10ns max.Sourse Impedance=50Ω
trr
+0.5A
0
-0.25A
-1.0A
1cm
SET TIME BASE FOR
5/10ns/cm

■



Dim	Min	Max
A	4.80	5.20
A1	2.21	2.61
A2	1.85	2.15
b	1.11	1.36
b2	1.91	2.21
c	0.51	0.75
D	20.70	21.30
D1	16.25	16.85
E	15.50	16.10
E1	13.00	13.60
E2	4.80	5.20
E3	2.30	2.70
e	10.88 TYP	
L	19.62	20.22
L1	-	4.30
φP	3.40	3.80
φP1	-	7.30
S	6.15 TYP	

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